Ref#	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	56	(word adj line wordline) near3 (Ti titanium) and DRAM	US:PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 18:56
S96	245	SGT and DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S97	536	finfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09:09:11
S98	72	S97 and DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S99	243	S96 not S98	US-PGPUB; USPAT; USOCR; EPO; IPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09:09:11
S100	889	(SGT surround\$3 adj gate) and (DRAM memory adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S101	644	S100 not S96	US-PGPUB, USPAT; USOCR; EPO; JPO; DERWENT ; IBM TDB	OR	ON	2005/11/09 09:11
S102	755	(257/329).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/09 09:11
S103	162	S102 and (memory DRAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11
S104	717	(257/300).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/09 09:11
S105	1	(leslie near3 terrence).in.	US-PGPUB; USPAT; USOCR, EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:11

S106	72	S97 and DRAM	US-PGPUB;	OR	ON	2005/11/09 09:11
			USPAT; USOCR; EPO; JPO;			
			DERWENT ; IBM_TDB			
S107	42	(maeda near3 shigenobu),in. and DRAM	US-PGPUB;	OR	ON	2005/11/09 09:11
			USPAT; USOCR; EPO; JPO;			
			DERWENT , IBM_TDB			
S110	7	S102 and undoped near3 channel	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:11
			USOCR; EPO; JPO;			
		·	DERWENT ; IBM_TDB			
S111	107	(438/269).CCLS.	US-PGPUB; USPAT:	OR	OFF	2005/11/09 09:11
			USOCR; EPO; JPO;			
			DERWENT ; IBM_TDB			
S112	122	S103 not (S96 S98 S101)	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:11
			USOCR; EPO; JPO;			
			DERWENT ; IBM_TDB			
S113	235	S99 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:11
			USOCR; EPO; JPO;			
			DERWENT , IBM_TDB			
S114	601	S101 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:11
		•	USOCR; EPO; JPO;			
			DERWENT ; IBM_TDB			
S115	9.	vertical adj (transistor channel) not trench and channel near2 undopéd	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:11
			USOCR; EPO; JPO;			
			DERWENT , IBM_TDB			
S116	657	(fin adj fet finfet)	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:11
			USOCR; EPO; JPO;			
:::::::::::::::::::::::::::::::::::::::			DERWENT ; IBM_TDB			
S117	92	S116 and DRAM	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:11
			USOCR, EPO; JPO; DERWENT			
~			, IBM_TDB			
S118	20	S117 not S98	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:11
		·	USOCR; EPO; JPO; DERWENT			
0110	rea	72.272.172.2	; IBM_TDB			
S119	657	(finfet fin adj fet)	US-PGPUB; USPAT; USOCR;	OR	ON	2005/11/09 09:26
			EPO; JPO; DERWENT			
			;IBM_TDB			

S120	580	S119 not (S103 S96 S98 S101)	US-PGPUB;	OR	ON	2005/11/09 09:28
			USPAT; USOCR;			
			EPO; JPO; DERWENT ; IBM_TDB			
S121	455	S120 and (@ad<"20040127" @rlad<"20040127").	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:28
			USOCR; EPO; JPO;			
Giaa	450	507 (0102 504 508 5101)	; IBM_TDB	0.0	O 1 7	200 6 14 4 100 00 40
S122	459	S97 not (S103 S96 S98 S101)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/11/09 09:42
S123	376	S122 and (@ad<"20040127" @rlad<"20040127")	; IBM_TDB US-PGPUB;	OR	ON	2005/11/09 09:43
	2,0	0122 alia (@aa * 20070127 @11aa * 20070127	USPAT; USOCR;	OK.	OIN	2003/11/09 09.43
			EPO; JPO; DERWENT			
S124	79	S121 not S123	US-PGPUB;	OR	ON	2005/11/09 09:40
	·		USPAT; USOCR; EPO; JPO; DERWENT ; IBM TDB			
S125	1502	vertical adj (FET MOSFET transistor channel) and (DRAM dynamic adj RAM)	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:54
			USOCR; EPO; JPO;			
			DERWENT ; IBM_TDB			
S126	1232	S125 not (S119 S112 S106 S103 S96 S98 S101)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 09:55
S127	1173	S126 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:56
			USOCR; EPO; JPO;			
S128	573	S127 not trench.ab.	DERWENT; IBM_TDB	O.D.	ov.	2005/11/00 00 55
5126	373	5127 not genen.au.	USPAT; USOCR;	OR	ON	2005/11/09 09:55
			EPO; JPO; DERWENT			
S129	1363	vertical adj (FET MOSFET transistor channel) and (DRAM dynamic adj RAM memory adj cell) and capacitor	; IBM_TDB US-PGPUB;	OR	ON	2005/11/09 09:54
		menory auf centrant capaciwi	USPAT; USOCR; EPO; JPO;			
			DERWENT ; IBM_TDB			
S130	651	S129 not trench.ab.	US-PGPUB; USPAT;	OR	ON	2005/11/09 09:55
			USOCR; EPO; JPO; DERWENT			
S131	489	S130 not (S119 S112 S106 S103 S96 S98 S101)	; IBM_TDB US-PGPUB;	OR	ON	2005/11/09 09:55
	707	2.20 00.10.10.10.00.00.00.00.00.00.00.00.00.0	USPAT; USOCR;	UK.	ŲIN.	2003/11/09/09:33
, ,			EPO; JPO; DERWENT			
			; IBM_TDB			

S132	464	S131 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 14:59
S133	2063	(257/306).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/09 10:01
S142	18	(lucien near3 bissey).in.	USPAT	OR	ON	2005/11/09 11:47
S143	20	(thomas near3 voshell).in.	USPAT	OR	ON	2005/11/09 11:48
S144	108	(kevin near3 duesman).in.	USPAT	OR	ON	2005/11/09 11:49
S145	104	S144 not (S143 S142)	USPAT	OR	ON	2005/11/09 11:50
S146	9	undoped near channel and (SGT vmos vertical adj (FET MOSFET transistor channel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 14:11
S147	57	(intrinsic undoped) near2 channel and (SGT vmos vertical adj (FET MOSFET MOS transistor channel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 14:11
S148	58	(intrinsic undoped) near2 channel and (SGT vmos vertical adj (FET MOSFET MISFET MOS transistor channel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/09 17:08
S149	2	("5451538"),PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/09:14:59